



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts,Customers Priority,Honest Operation,and Considerate Service",our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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General Description

- Advanced High Voltage MOSFET technology
- Low $R_{DS(ON)}$
- Low C_{iss} and C_{rss}
- High Current Capability
- RoHS and Halogen Free Compliant

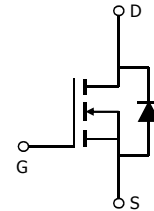
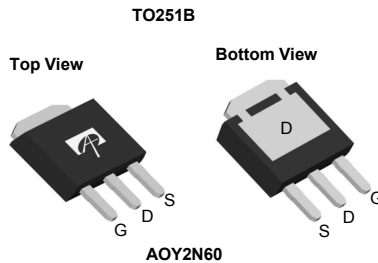
Applications

- General Lighting for LED and CCFL
- AC/DC Power supplies for Industrial, Consumer, and Telecom

Product Summary

V_{DS} @ $T_{j,max}$	700V
I_D (at $V_{GS}=10V$)	2A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	< 4.7 Ω

100% UIS Tested
 100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOY2N60	TO-251B	Tube	4000

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current ^B	I_D	$T_C=25^\circ\text{C}$	2
		$T_C=100^\circ\text{C}$	1.4
Pulsed Drain Current ^C	I_{DM}	6	A
Avalanche Current ^{C,I}	I_{AR}	4.6	A
Repetitive avalanche energy ^{C,I}	E_{AR}	10.6	mJ
Single pulsed avalanche energy ^H	E_{AS}	97	mJ
Peak diode recovery dv/dt	dv/dt	5	V/ns
Power Dissipation ^B	P_D	$T_C=25^\circ\text{C}$	57
		Derate above 25°C	0.45
Junction and Storage Temperature Range	T_J, T_{STG}	-50 to 150	$^\circ\text{C}$
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient ^{A,G}	$R_{\theta JA}$	40	50	$^\circ\text{C/W}$
Maximum Case-to-sink ^A	$R_{\theta CS}$	-	0.5	$^\circ\text{C/W}$
Maximum Junction-to-Case ^{D,F}	$R_{\theta JC}$	1.8	2.2	$^\circ\text{C/W}$

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V, T _J =25°C	600			V
		I _D =250μA, V _{GS} =0V, T _J =150°C		700		
BV _{DSS} /ΔT _J	Zero Gate Voltage Drain Current	I _D =250μA, V _{GS} =0V		0.7		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600V, V _{GS} =0V			1	μA
		V _{DS} =480V, T _J =125°C			10	
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} =±30V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =5V, I _D =250μA	3.4	4	4.5	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =1A		3.9	4.7	Ω
g _{FS}	Forward Transconductance	V _{DS} =40V, I _D =1A		2.8		S
V _{SD}	Diode Forward Voltage	I _S =1A, V _{GS} =0V		0.79	1	V
I _S	Maximum Body-Diode Continuous Current				2	A
I _{SM}	Maximum Body-Diode Pulsed Current ^C				6	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, f=1MHz		295		pF
C _{oss}	Output Capacitance			30		pF
C _{rss}	Reverse Transfer Capacitance			2.3		pF
R _g	Gate resistance	f=1MHz		3.2		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =10V, V _{DS} =480V, I _D =2A		6.5	11	nC
Q _{gs}	Gate Source Charge			1.5		nC
Q _{gd}	Gate Drain Charge			1.8		nC
t _{D(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =300V, I _D =2A, R _G =25Ω		16		ns
t _r	Turn-On Rise Time			11		ns
t _{D(off)}	Turn-Off Delay Time			28		ns
t _f	Turn-Off Fall Time			14		ns
t _{rr}	Body Diode Reverse Recovery Time	I _F =2A, dI/dt=100A/μs, V _{DS} =100V		268		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =2A, dI/dt=100A/μs, V _{DS} =100V		1.6		μC

A. The value of R_{θJA} is measured with the device in a still air environment with T_A=25°C.

B. The power dissipation P_D is based on T_{J(MAX)}=150°C in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C.

D. The R_{θJA} is the sum of the thermal impedance from junction to case R_{θJC} and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)}=150°C.

G. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C.

H. L=60mH, I_{AS}=1.8A, V_{DD}=150V, R_G=10Ω, Starting T_J=25°C.

I. L=1.0mH, V_{DD}=150V, R_G=25Ω, Starting T_J=25°C.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

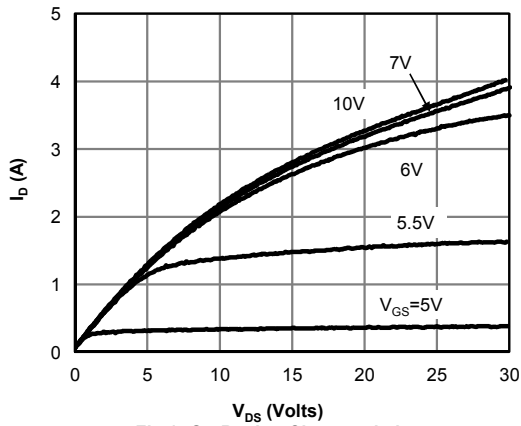


Figure 1: On-Region Characteristics

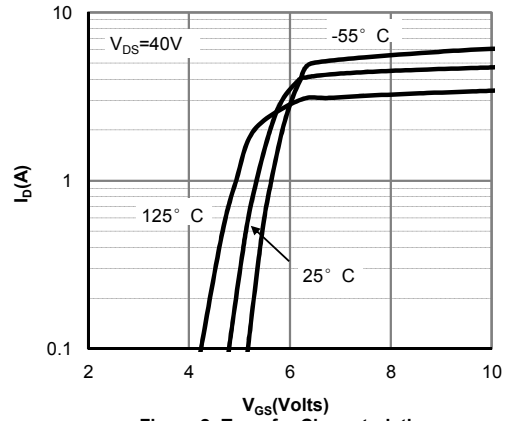


Figure 2: Transfer Characteristics

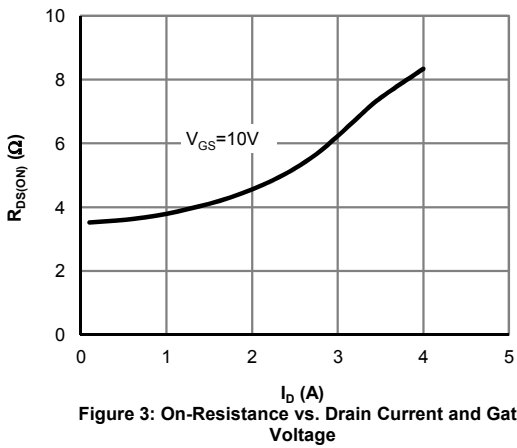


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

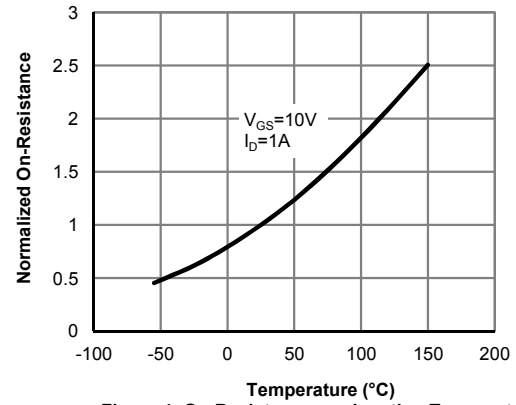


Figure 4: On-Resistance vs. Junction Temperature

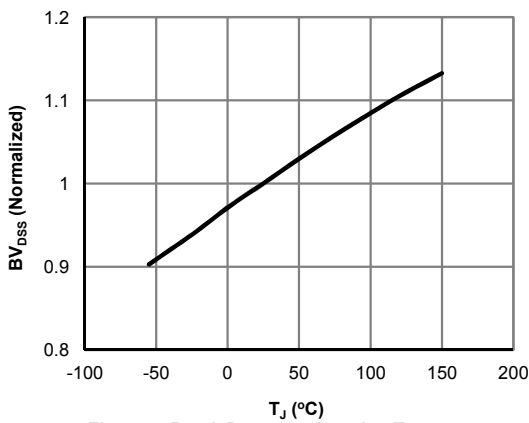


Figure 5: Break Down vs. Junction Temperature

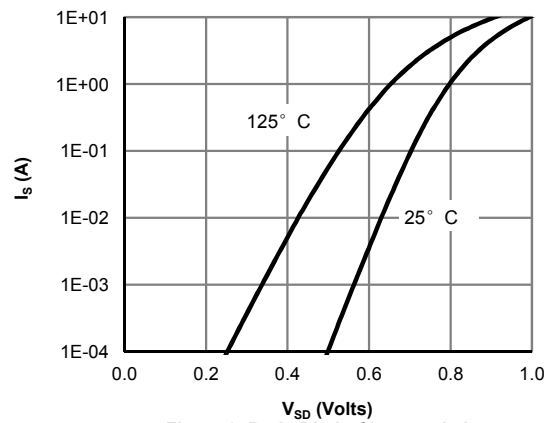


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

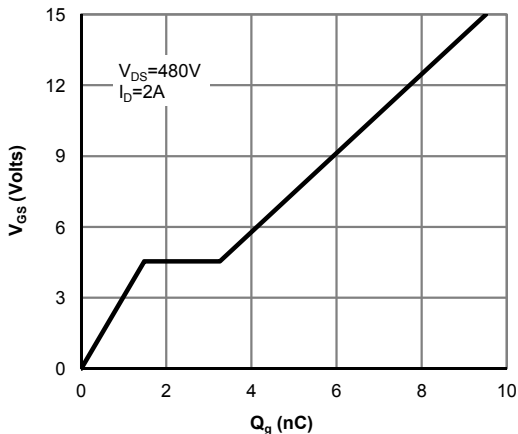


Figure 7: Gate-Charge Characteristics

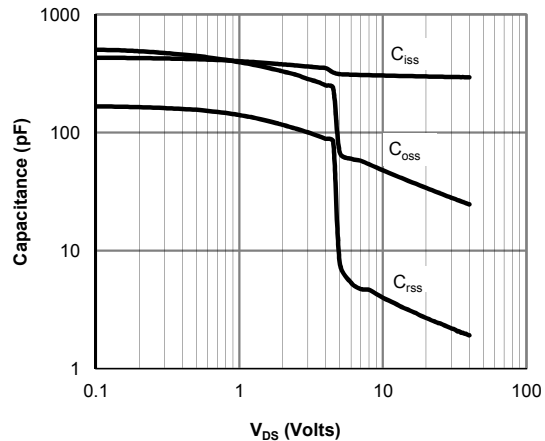


Figure 8: Capacitance Characteristics

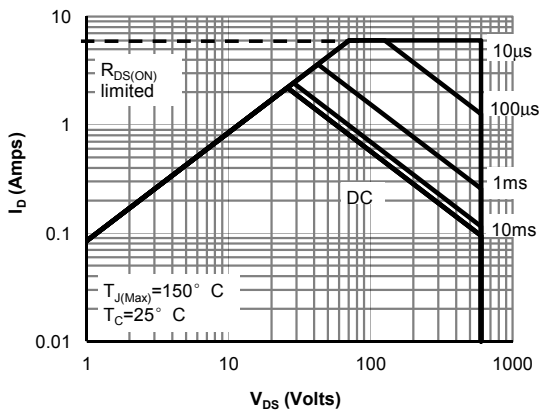


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

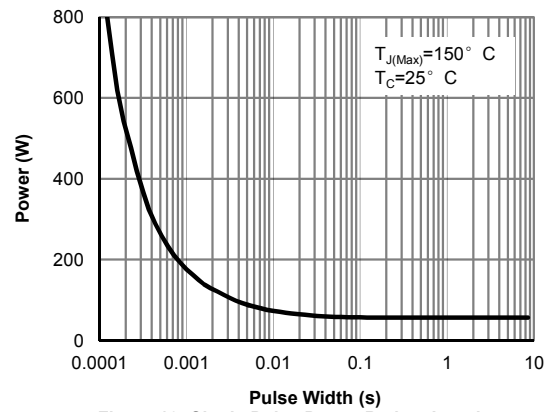


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

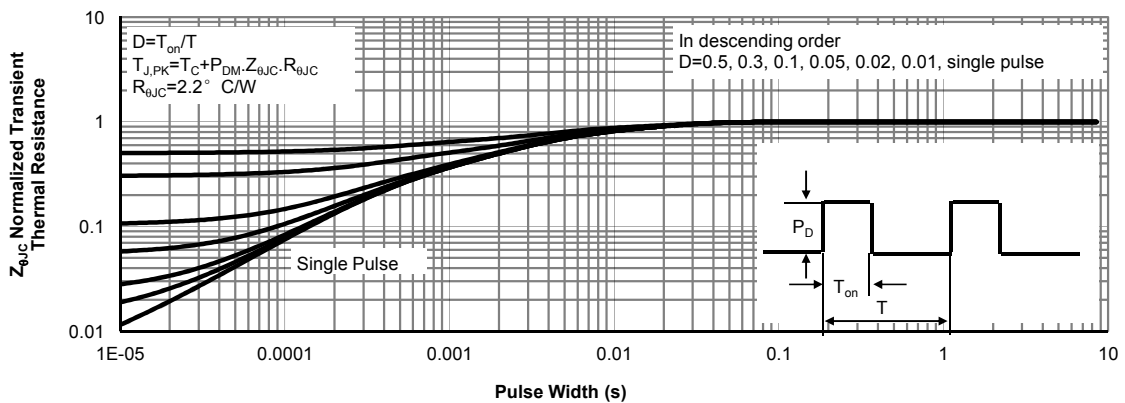


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

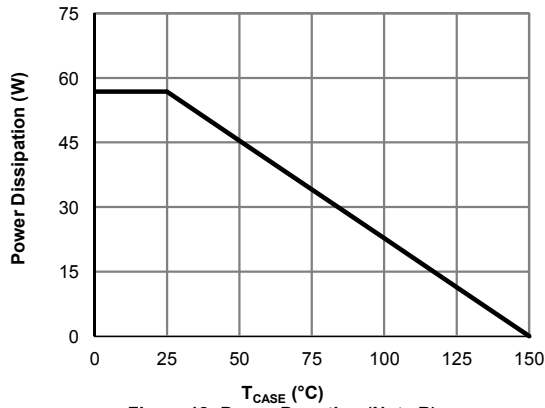


Figure 12: Power De-rating (Note B)

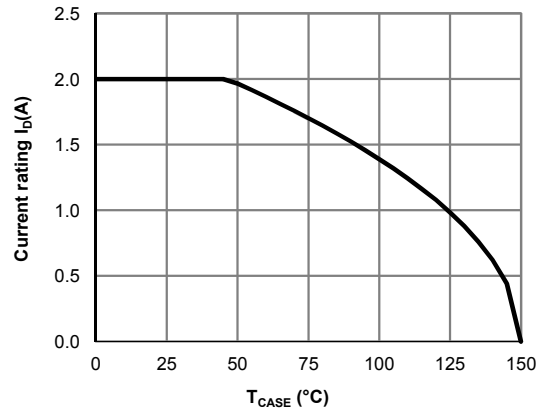


Figure 13: Current De-rating (Note B)

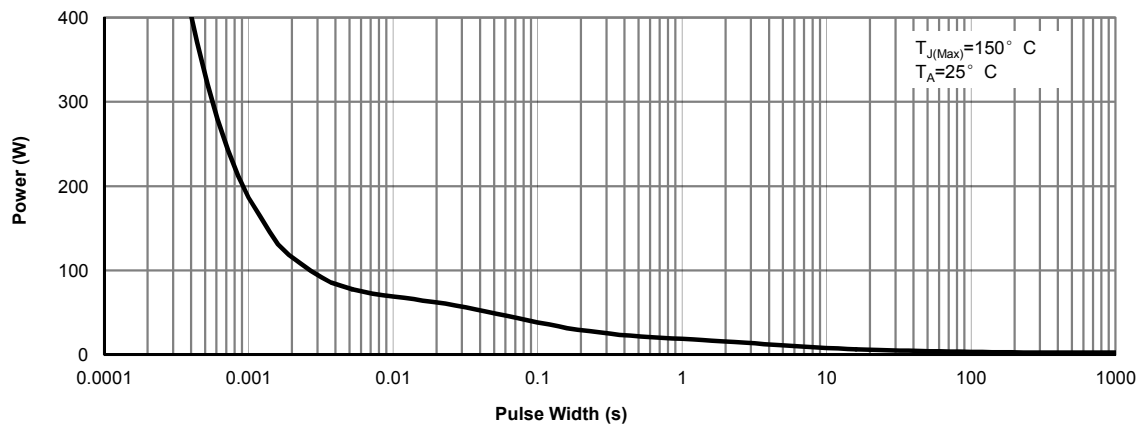


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

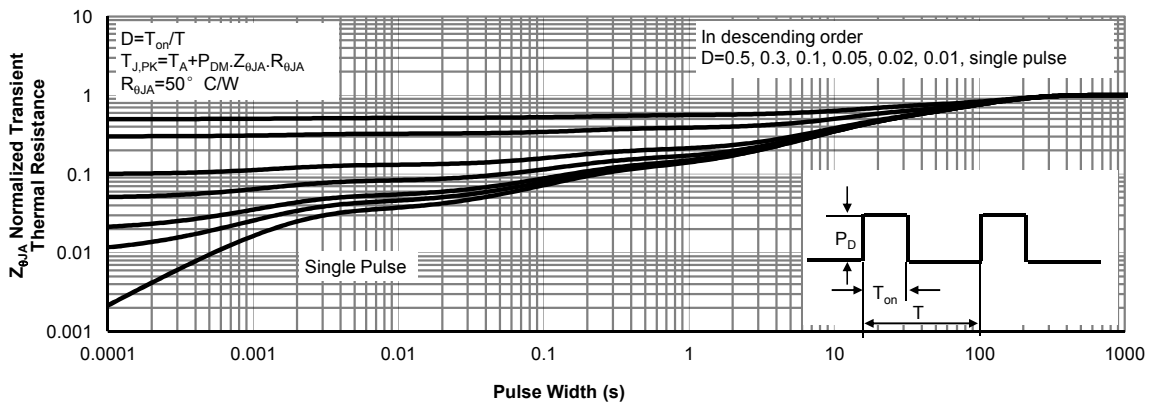
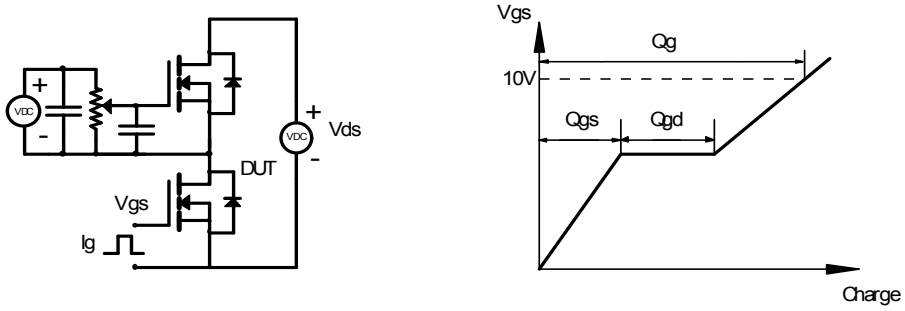
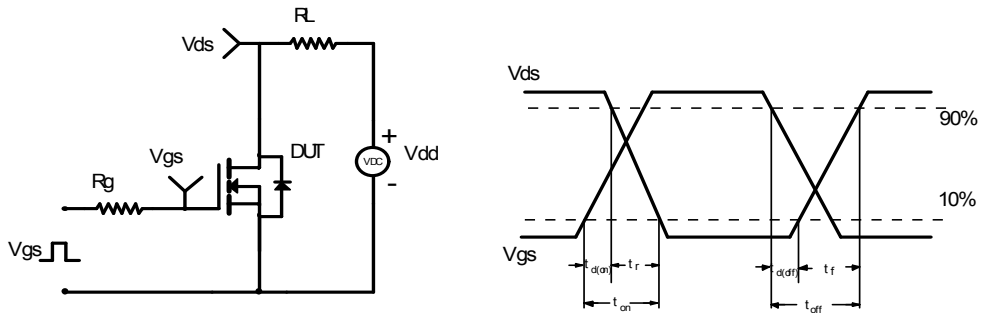


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

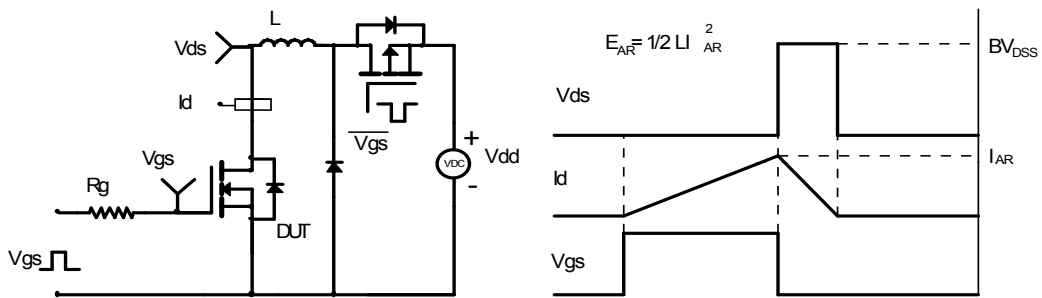
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

